

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

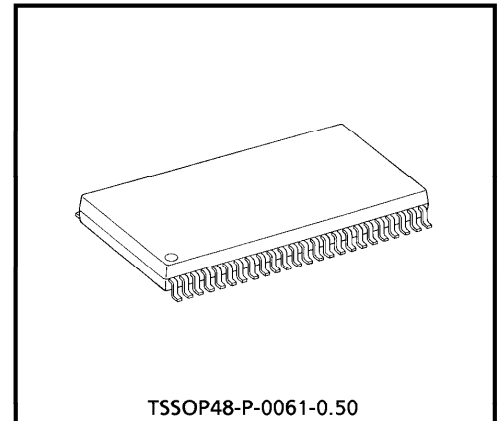
**TC74LCX163245FT****16-BIT DUAL SUPPLY VOLTAGE  
INTERFACE BUS TRANSCEIVER**

The TC74LCX163245 is a dual supply, advanced high speed CMOS 16 bit DUAL SUPPLY VOLTAGE INTERFACE BUS TRANSCEIVER fabricated with silicon gate CMOS technology.

Designed for use as an interface between a 3.3 V or 2.5 V bus and a 5 V bus in mixed 3.3 V or 2.5 V/5 V supply systems' it achieves high speed operation while maintaining the CMOS low power dissipation.

It is intended for 2 way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input. The enable input ( $\overline{OE}$ ) can be used to disable the device so that the busses are effectively isolated. The B-port interfaces with the 3 V or 2.5 V bus, the A-port with the 5 V bus.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.



TSSOP48-P-0061-0.50

Weight : 0.25 g (Typ.)

**FEATURES**

- Bidirectional interface between 3.3 V or 2.5 V and 5 V buses
- High speed :  $t_{pd} = 7.0 \text{ ns (max)}$   
( $V_{CCB} = 3.3 \pm 0.3 \text{ V} / V_{CCA} = 5 \pm 0.5 \text{ V}$ ,  $T_a = -40 \sim 85^\circ\text{C}$ )
- Low power dissipation :  $I_{CC} = 80 \mu\text{A (max)}$  ( $T_a = -40 \sim 85^\circ\text{C}$ )
- Symmetrical output impedance :  $I_{OUTB} = \pm 24 \text{ mA (min)}$   
 $I_{OUTA} = \pm 24 \text{ mA (min)}$   
( $V_{CCB} = 3.0 \text{ V} / V_{CCA} = 4.5 \text{ V}$ )
- Power Down Protection is provided on all inputs and outputs.
- Allows A port and  $V_{CCA}$  to float simultaneously when  $\overline{OE}$  is "H".
- Latch-up performance :  $\pm 300 \text{ mA}$
- ESD performance : Machine model  $> \pm 200 \text{ V (Note 2)}$
- Package : TSSOP (Thin Shrink Small Outline Package)

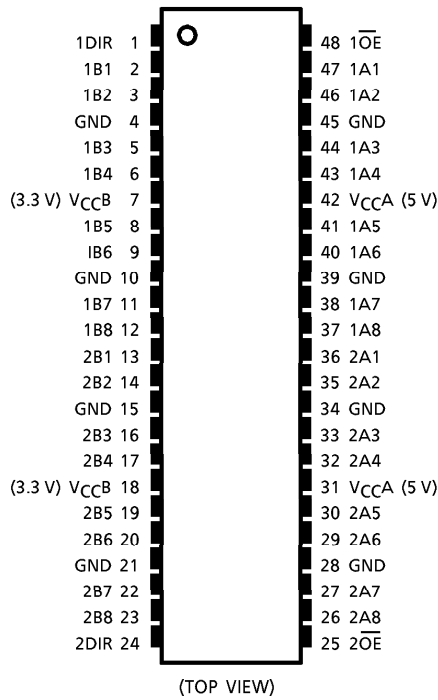
(Note 1) : Do not apply a signal to any bus terminal when it is in the output mode.  
Damage may result. All floating (high impedance) bus terminals must have their input fixed by means of pull up or pull down resistors.

(Note 2) : This device is electrostatic sensitivity (Human Body Model  $> 1 \text{ kV}$ ).  
Please handle with caution.

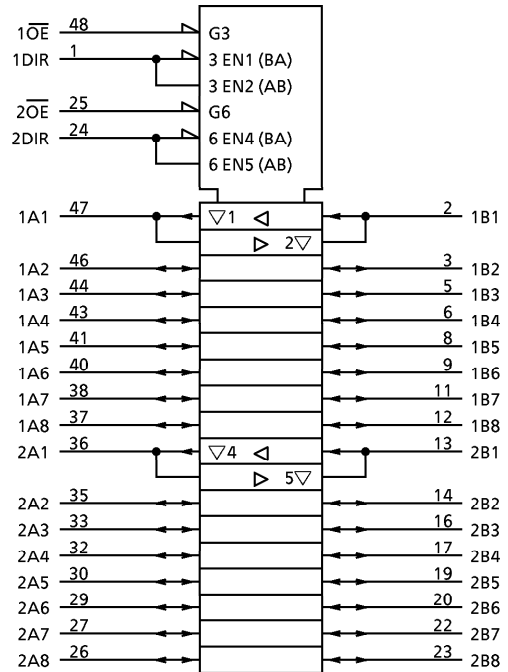
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**PIN CONNECTION**



**IEC LOGIC SYMBOL**



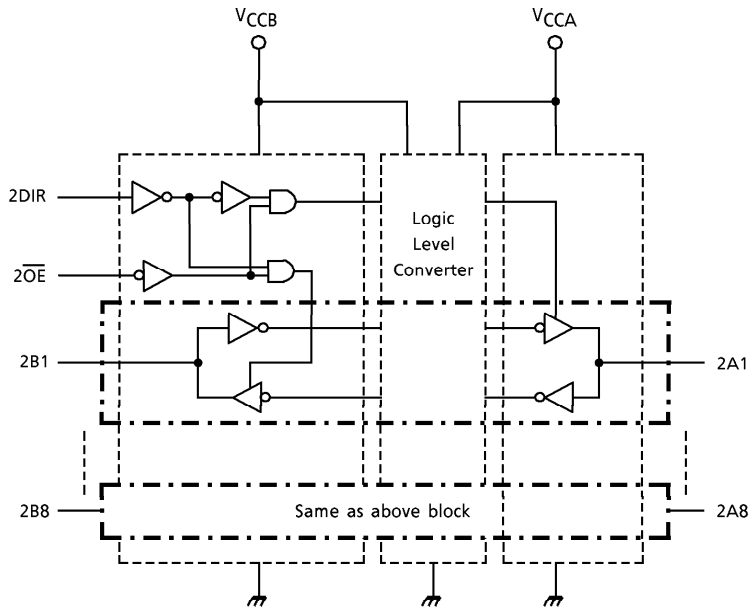
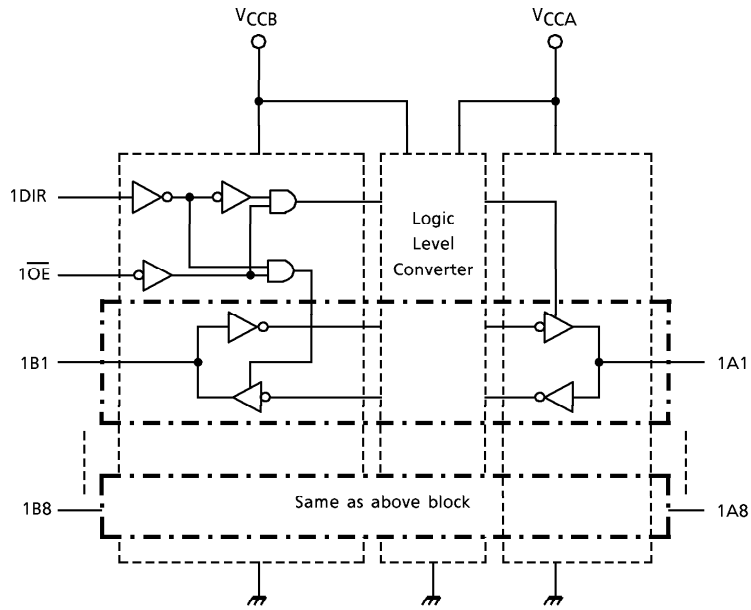
**TRUTH TABLE**

INPUT		FUNCTION		OUTPUT
$\overline{1OE}$	1DIR	BUS 1A1-1A8	BUS 1B1-1B8	
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	High Impedance		Z

INPUT		FUNCTION		OUTPUT
$\overline{2OE}$	2DIR	BUS 2A1-2A8	BUS 2B1-2B8	
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	High Impedance		Z

X : Don't Care  
 Z : High impedance

BLOCK DIAGRAM



**MAXIMUM RATINGS**

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage (Note 3)	V <sub>CCB</sub>	-0.5~7.0	V
	V <sub>CCA</sub>	-0.5~7.0	
DC Input Voltage	V <sub>IN</sub>	-0.5~7.0	V
DC Bus I/O Voltage	V <sub>I/OB</sub>	-0.5~7.0 (Note 4)	V
		-0.5~V <sub>CCB</sub> + 0.5 (Note 5)	
	V <sub>I/OA</sub>	-0.5~7.0 (Note 4)	
		-0.5~V <sub>CCA</sub> + 0.5 (Note 5)	
Input Diode Current	I <sub>IK</sub>	- 50	mA
Output Diode Current	I <sub>I/OK</sub>	± 50 (Note 6)	mA
DC Output Current	I <sub>OUTB</sub>	± 50	mA
	I <sub>OUTA</sub>	± 50	
DC V <sub>CC</sub> /Ground Current Per Supply Pin	I <sub>CCB</sub>	± 100	mA
	I <sub>CCA</sub>	± 100	
Power Dissipation	P <sub>D</sub>	400	mW
Storage Temperature	T <sub>stg</sub>	- 65~150	°C

(Note 3) : Don't supply a voltage to V<sub>CCA</sub> terminal when V<sub>CCB</sub> is in the off-state.

(Note 4) : Off-State

(Note 5) : High or Low State. I<sub>OUT</sub> absolute maximum rating must be observed.

(Note 6) : V<sub>OUT</sub> < GND, V<sub>OUT</sub> > V<sub>CC</sub>

**RECOMMENDED OPERATING RANGE**

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V <sub>CCB</sub>	2.3~3.6	V
	V <sub>CCA</sub>	4.5~5.5	
Input Voltage (DIR, $\overline{OE}$ )	V <sub>IN</sub>	0~5.5	V
Bus I/O Voltage	V <sub>I/OB</sub>	0~5.5 (Note 7)	V
		0~V <sub>CCB</sub> (Note 8)	
	V <sub>I/OA</sub>	0~5.5 (Note 7)	
		0~V <sub>CCA</sub> (Note 8)	
Output Current	I <sub>OUTB</sub>	± 24 (Note 9)	mA
		± 8 (Note 10)	
	I <sub>OUTA</sub>	± 24 (Note 11)	
Operating Temperature	T <sub>opr</sub>	- 40~85	°C
Input Rise and Fall Time	dt/dv	0~10 (V <sub>CCB</sub> = 2.3~3.6 V)	ns/V
		0~10 (V <sub>CCA</sub> = 4.5~5.5 V)	

(Note 7) : Off-State

(Note 8) : High or Low State

(Note 9) : V<sub>CCB</sub> = 3.0~3.6 V

(Note 10) : V<sub>CCB</sub> = 2.3~2.7 V

(Note 11) : V<sub>CCA</sub> = 4.5~5.5 V

## ELECTRICAL CHARACTERISTICS

## DC Characteristics

PARAMETER	SYM-BOL	TEST CONDITION	V <sub>CCB</sub> (V)	V <sub>CCA</sub> (V)	Ta = -40~85°C		UNIT	
					MIN	MAX		
"H" Level Input Voltage	V <sub>IHB</sub>	DIR, $\overline{OE}$ , Bn	2.5 ± 0.2	5.0 ± 0.5	1.7	—	V	
			3.3 ± 0.3	5.0 ± 0.5	2.0	—		
	V <sub>IHA</sub>	An	2.3~3.6	5.0 ± 0.5	2.0	—		
"L" Level Input Voltage	V <sub>ILB</sub>	DIR, $\overline{OE}$ , Bn	2.5 ± 0.2	5.0 ± 0.5	—	0.7	V	
			3.3 ± 0.3	5.0 ± 0.5	—	0.8		
	V <sub>ILA</sub>	An	2.3~3.6	5.0 ± 0.5	—	0.8		
"H" Level Output Voltage	V <sub>OHB</sub>	V <sub>INA</sub> = V <sub>IHA</sub> or V <sub>ILA</sub> V <sub>INB</sub> = V <sub>IHB</sub> or V <sub>ILB</sub>	I <sub>OHB</sub> = -100 μA	2.3~3.6	5.0 ± 0.5	V <sub>CCB</sub> - 0.2	—	V
			I <sub>OHB</sub> = -24 mA	3.0	5.0 ± 0.5	2.2	—	
			I <sub>OHB</sub> = -8 mA	2.3	5.0 ± 0.5	1.8	—	
	V <sub>OHA</sub>	V <sub>INA</sub> = V <sub>IHA</sub> or V <sub>ILA</sub> V <sub>INB</sub> = V <sub>IHB</sub> or V <sub>ILB</sub>	I <sub>OHA</sub> = -100 μA	2.3~3.6	5.0 ± 0.5	V <sub>CCA</sub> - 0.2	—	
			I <sub>OHA</sub> = -24 mA	2.3~3.6	4.5	3.8	—	
			I <sub>OHA</sub> = -8 mA	2.3~3.6	4.5	—	—	
"L" Level Output Voltage	V <sub>OLB</sub>	V <sub>INA</sub> = V <sub>IHA</sub> or V <sub>ILA</sub> V <sub>INB</sub> = V <sub>IHB</sub> or V <sub>ILB</sub>	I <sub>OHB</sub> = 100 μA	2.3~3.6	5.0 ± 0.5	—	0.2	V
			I <sub>OHB</sub> = 24 mA	3.0	5.0 ± 0.5	—	0.55	
			I <sub>OHB</sub> = 8 mA	2.3	5.0 ± 0.5	—	0.6	
	V <sub>OLA</sub>	V <sub>INA</sub> = V <sub>IHA</sub> or V <sub>ILA</sub> V <sub>INB</sub> = V <sub>IHB</sub> or V <sub>ILB</sub>	I <sub>OHA</sub> = 100 μA	2.3~3.6	5.0 ± 0.5	—	0.2	
			I <sub>OHA</sub> = 24 mA	2.3~3.6	4.5	—	0.44	
			I <sub>OHA</sub> = 8 mA	2.3~3.6	4.5	—	—	
3-State Output Off-State Current	I <sub>OZB</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>I/OB</sub> = V <sub>CCB</sub> or GND	2.3~3.6	5.0 ± 0.5	—	± 5.0	μA	
	I <sub>OZA</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>I/OA</sub> = V <sub>CCA</sub> or GND	2.3~3.6	5.0 ± 0.5	—	± 5.0		
Input Leakage Current	I <sub>IN</sub>	V <sub>IN</sub> (DIR, $\overline{OE}$ ) = V <sub>CCB</sub> or GND	3.6	5.5	—	± 5.0	μA	
Power Off Leakage Current	I <sub>OFF</sub>	V <sub>INA</sub> , V <sub>INB</sub> = 0~5.5 V	0	0	—	10	μA	
Quiescent Supply Current	I <sub>CCB1</sub>	V <sub>I/OA</sub> = Open, V <sub>CCA</sub> = Open V <sub>INB</sub> = V <sub>CCB</sub> or GND $\overline{OE}$ = V <sub>CCB</sub> , DIR = GND	3.6	Open	—	50	μA	
	I <sub>CCB2</sub>	V <sub>INA</sub> = V <sub>CCA</sub> or GND V <sub>INB</sub> = V <sub>CCB</sub> or GND	3.6	5.5	—	50		
	I <sub>CCA</sub>	V <sub>INA</sub> = V <sub>CCA</sub> or GND V <sub>INB</sub> = V <sub>CCB</sub> or GND	3.6	5.5	—	80		
	I <sub>CCTB</sub>	V <sub>INB</sub> = V <sub>CCB</sub> - 0.6 V PER INPUT	3.6	5.0 ± 0.5	—	500		
	I <sub>CCTA</sub>	V <sub>INA</sub> = 3.4 V PER INPUT	2.3~3.6	5.5	—	2.0	mA	

**AC Characteristics** (Input  $t_r = t_f = 2.5 \text{ ns}$ ,  $R_L = 500 \Omega$ )  
 $V_{CCB} = 3.3 \pm 0.3 \text{ V}$

PARAMETER	SYMBOL	TEST CONDITION	CL (pF)	$V_{CCA}$ (V)	$T_a = -40 \sim 85^\circ\text{C}$		UNIT
					MIN	MAX	
Propagation Delay Time ( $B_n \Rightarrow A_n$ )	$t_{pLH}$ $t_{pHL}$	Input : $B_n$ Output : $A_n$ (DIR = "L")	50	$5.0 \pm 0.5$	1.0	6.0	ns
3-State Output Enable Time ( $\overline{OE} \Rightarrow A_n$ )	$t_{pZL}$ $t_{pZH}$		50	$5.0 \pm 0.5$	1.0	9.0	
3-State Output Disable Time ( $\overline{OE} \Rightarrow A_n$ )	$t_{pLZ}$ $t_{pHZ}$		50	$5.0 \pm 0.5$	1.0	9.0	
Propagation Delay Time ( $A_n \Rightarrow B_n$ )	$t_{pLH}$ $t_{pHL}$	Input : $A_n$ Output : $B_n$ (DIR = "H")	50	$5.0 \pm 0.5$	1.0	7.0	ns
3-State Output Enable Time ( $\overline{OE} \Rightarrow B_n$ )	$t_{pZL}$ $t_{pZH}$		50	$5.0 \pm 0.5$	1.0	9.0	
3-State Output Disable Time ( $\overline{OE} \Rightarrow B_n$ )	$t_{pLZ}$ $t_{pHZ}$		50	$5.0 \pm 0.5$	1.0	9.0	
Output to Output Skew	$t_{osLH}$ $t_{osHL}$	(Note 12)	50	$5.0 \pm 0.5$	—	1.0	ns

$V_{CCB} = 2.5 \pm 0.2 \text{ V}$

PARAMETER	SYMBOL	TEST CONDITION	CL (pF)	$V_{CCA}$ (V)	$T_a = -40 \sim 85^\circ\text{C}$		UNIT
					MIN	MAX	
Propagation Delay Time ( $B_n \Rightarrow A_n$ )	$t_{pLH}$ $t_{pHL}$	Input : $B_n$ Output : $A_n$ (DIR = "L")	50	$5.0 \pm 0.5$	1.0	8.0	ns
3-State Output Enable Time ( $\overline{OE} \Rightarrow A_n$ )	$t_{pZL}$ $t_{pZH}$		50	$5.0 \pm 0.5$	1.0	12.0	
3-State Output Disable Time ( $\overline{OE} \Rightarrow A_n$ )	$t_{pLZ}$ $t_{pHZ}$		50	$5.0 \pm 0.5$	1.0	12.0	
Propagation Delay Time ( $A_n \Rightarrow B_n$ )	$t_{pLH}$ $t_{pHL}$	Input : $A_n$ Output : $B_n$ (DIR = "H")	30	$5.0 \pm 0.5$	1.0	9.0	ns
3-State Output Enable Time ( $\overline{OE} \Rightarrow B_n$ )	$t_{pZL}$ $t_{pZH}$		30	$5.0 \pm 0.5$	1.0	12.0	
3-State Output Disable Time ( $\overline{OE} \Rightarrow B_n$ )	$t_{pLZ}$ $t_{pHZ}$		30	$5.0 \pm 0.5$	1.0	10.0	
Output to Output Skew	$t_{osLH}$ $t_{osHL}$	(Note 12)	30 or 50	$5.0 \pm 0.5$	—	1.0	ns

(Note 12) : Parameter guaranteed by design.  
 $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

Capacitive characteristics (Ta = 25°C)  
VCCB = 2.5, 3.3 V

PARAMETER	SYMBOL	TEST CONDITION	VCCA (V)	TYP.	UNIT
Input Capacitance	C <sub>IN</sub>	DIR, $\overline{OE}$	5.0	7	pF
Output Capacitance	C <sub>I/O</sub>	An, Bn	5.0	8	pF
Power Dissipation Capacitance (Note 13)	C <sub>PDA</sub>	A ⇒ B (DIR = "H")	5.0	20	pF
		B ⇒ A (DIR = "L")	5.0	66	
	C <sub>PDB</sub>	A ⇒ B (DIR = "H")	5.0	34	
		B ⇒ A (DIR = "L")	5.0	4	

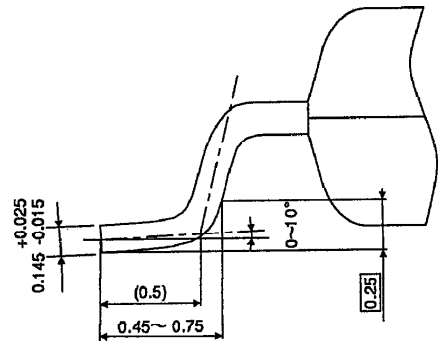
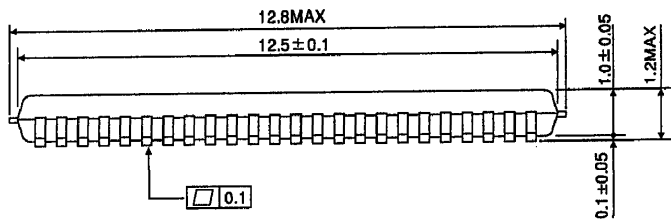
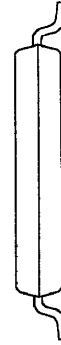
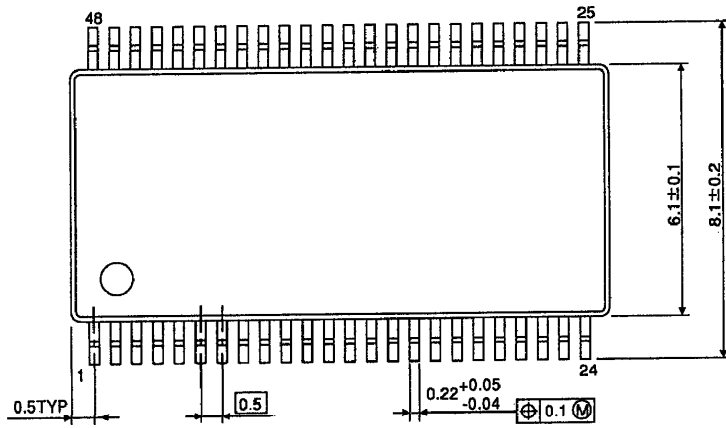
(Note 13) : C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16 \text{ (per bit)}$$

**PACKAGE DIMENSIONS**  
TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25 g (Typ.)